

Title (en)

WAFER STRUCTURE FOR ELECTRONIC INTEGRATED CIRCUIT MANUFACTURING

Title (de)

WAFERSTRUKTUR ZUR HERSTELLUNG EINER ELEKTRONISCHEN INTEGRIERTEN SCHALTUNG

Title (fr)

STRUCTURE DE TRANCHE POUR LA FABRICATION DE CIRCUITS INTÉGRÉS ÉLECTRONIQUES

Publication

EP 2748845 A4 20150708 (EN)

Application

EP 12825755 A 20120824

Priority

- US 201113218308 A 20110825
- US 201113218273 A 20110825
- US 201113218335 A 20110825
- US 201113218345 A 20110825
- US 201113218352 A 20110825
- US 201113218292 A 20110825
- US 2012052302 W 20120824

Abstract (en)

[origin: WO2013028973A1] A bonded wafer structure having a handle wafer, a device wafer, and an interface region with an abrupt transition between the conductivity profile of the device wafer and the handle wafer is used for making semiconductor devices. The improved doping profile of the bonded wafer structure is well suited for use in the manufacture of integrated circuits. The bonded wafer structure is especially suited for making radiation-hardened integrated circuits.

IPC 8 full level

H01L 21/8238 (2006.01); **H01L 21/263** (2006.01); **H01L 27/092** (2006.01); **H01L 29/32** (2006.01); **H01L 29/868** (2006.01)

CPC (source: EP)

H01L 21/187 (2013.01); **H01L 21/263** (2013.01); **H01L 27/088** (2013.01); **H01L 27/092** (2013.01); **H01L 29/32** (2013.01); **H01L 29/36** (2013.01); **H01L 29/66136** (2013.01); **H01L 29/868** (2013.01)

Citation (search report)

- [Y] DE 3435464 A1 19860410 - BOSCH GMBH ROBERT [DE]
- [Y] US 4240844 A 19801223 - BARTKO JOHN [US], et al
- [Y] WO 9209099 A1 19920529 - BOSCH GMBH ROBERT [DE]
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- [A] A. OCHOA ET AL: "Latch-Up Control in CMOS Integrated Circuits", IEEE TRANSACTIONS ON NUCLEAR SCIENCE, vol. 26, no. 6, 1 December 1979 (1979-12-01), pages 5065 - 5068, XP055191893, ISSN: 0018-9499, DOI: 10.1109/TNS.1979.4330274
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- See references of WO 2013028988A1

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

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DOCDB simple family (application)

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